April 1999 ADVANCE INFORMATION

# FDD6030BL

# **FAIRCHILD** SEMICONDUCTOR IM

# **FDD6030BL** N-Channel PowerTrench<sup>™</sup> MOSFET

#### **General Description**

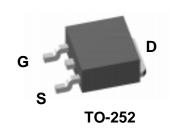
This N-Channel Logic level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the onstate resistance and yet maintain low gate charge for superior switching performance.

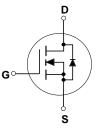
#### Applications

- DC/DC converter
- Motor drives

#### Features

- 35 A, 30 V.  $R_{DS(ON)} = 0.018 \ \Omega \ @ V_{GS} = 10 \ V$  $R_{DS(ON)} = 0.025 \ \Omega \ @ V_{GS} = 4.5 \ V.$
- Low gate charge.
- Fast switching speed.
- High performance trench technology for extremely low  $\rm R_{\rm DS(ON)}.$





## Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage		30	V	
V <sub>GSS</sub>	Gate-Source Voltage		±20	V	
ID	Maximum Drain Current -Continuous	(Note 1)	35	А	
		(Note 1a)	9		
	Maximum Drain Current -Pulsed		100		
PD	Maximum Power Dissipation @ T <sub>c</sub> = 25°C	(Note 1)	44	W	
	$T_{A} = 25^{\circ}C \qquad ($	(Note 1a)	2.8		
	$T_{A} = 25^{\circ}C \qquad ($	(Note 1b)	1.3		
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Ra	ange	-55 to +150	°C	

## **Thermal Characteristics**

R <sub>θJA</sub> Thermal Resistance, Junction-to- Ambient         (Note 1b)         96         °C/W	R <sub>θ</sub> JC	Thermal Resistance, Junction-to- Case	(Note 1)	2.8	°C/W
	$R_{\theta^{JA}}$	Thermal Resistance, Junction-to- Ambient	(Note 1b)	96	°C/W

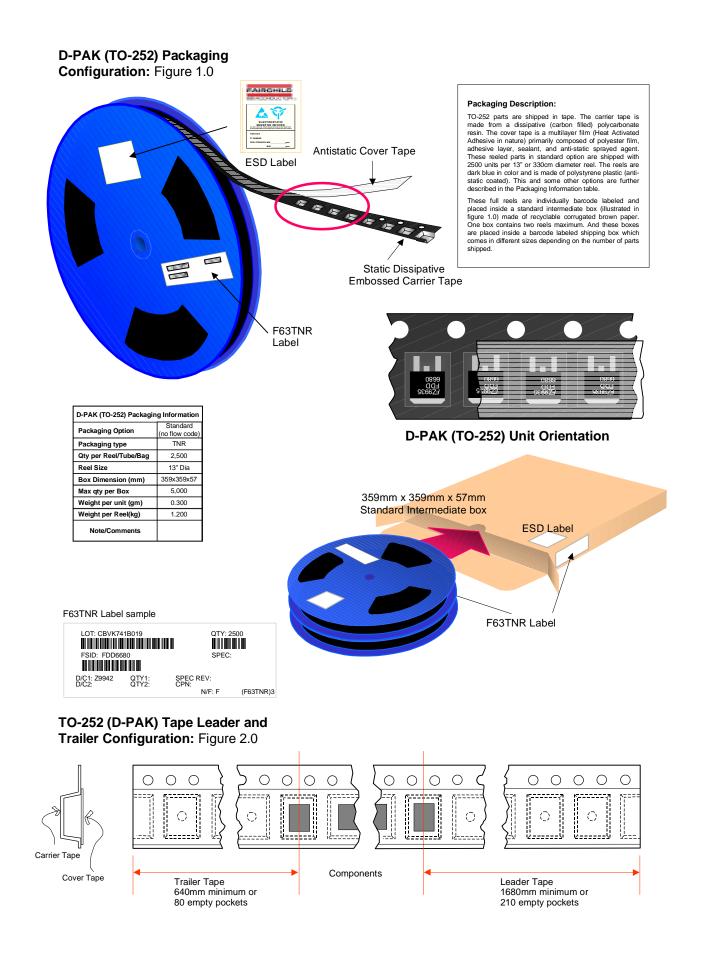
## Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6030BL	FDD6030BL	13"	16mm	2500

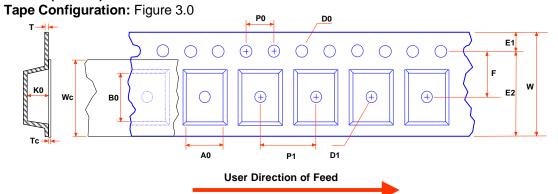
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
	IARACTERISTICS					
<u>OFF CF</u> BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	30	r		V
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
GSSF	Gate-Body Leakage, Forward	$V_{\rm DS} = 20$ V, $V_{\rm DS} = 0$ V			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
<u>ON CHA</u> V <sub>GS(TH)</sub>	ARACTERISTICS (Note 2) Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1	<u> </u>	3	V
R <sub>DS(ON)</sub>	Static Drain-Source	$V_{GS} = V_{GS}, H_D = 230 \mu A$ $V_{GS} = 10  V, I_D = 9  A$			0.018	Ω
COS(ON)	On-Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$			0.025	32
	SOURCE DIODE CHARACTE	RISTICS AND MAXIMUM F		:		
s	Maximum Continuous Drain-Source			Í	2.3	А
V <sub>SD</sub>	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 2.3 \text{ A}$			1.3	V
	a) $R_{a,A} = 45^{\circ}C.W$ when r 1in <sup>2</sup> pad of 2oz copper. on letter size paper Pulse Width $\leq 300 \ \mu$ s, Duty Cycle $\leq 2.0\%$		<sub>AJA</sub> = 96 <sup>0</sup> C/W wh mum pad.	en mounted	on a	
	<ul> <li>1in<sup>2</sup> pad of 2oz copper.</li> <li>on letter size paper</li> </ul>			ien mounted	on a	
	<ul> <li>1in<sup>2</sup> pad of 2oz copper.</li> <li>on letter size paper</li> </ul>			ien mounted	on a	
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FDD6030BL Rev. A



### D-PAK (TO-252) Embossed Carrier



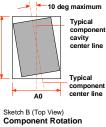
	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	К0	т	Wc	Тс
<b>TO252</b> (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

В0

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



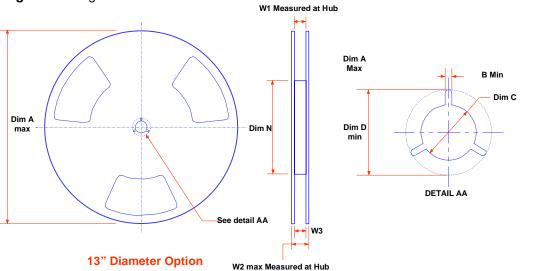
Sketch A (Side or Front Sectional View) Component Rotation





Sketch C (Top View) Component lateral movement

D-PAK (TO-252) Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim A         Dim B         Dim C         Dim D         Dim N         Dim W1         Dim W2         Dim W3 (LS)					Dim W3 (LSL-USL)	
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4

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